

Ideal Strength of Doped Graphene

S. J. Woo and Young-Woo Son*

Korea Institute for Advanced Study, Seoul 130-722, Korea

(Dated: November 9, 2012)

While the mechanical distortions change the electronic properties of graphene significantly, the effects of electronic manipulation on its mechanical properties have not been known. Using first-principles calculation methods, we show that, when graphene expands isotropically under equibiaxial strain, both the electron and hole doping can maintain or improve its ideal strength slightly and enhance the critical breaking strain dramatically. Contrary to the isotropic expansions, the electron doping decreases the ideal strength as well as critical strain of uniaxially strained graphene while the hole doping increases the both. Distinct failure mechanisms depending on type of strains are shown to be origins of the different doping induced mechanical stabilities. Our findings may resolve a contradiction between recent experimental and theoretical results on the strength of graphene.

PACS numbers: 62.20.-x, 63.20.kd, 63.22.Rc, 81.40.Jj

A defect-free infinite crystal becomes mechanically unstable at a stress with a corresponding critical strain. Such a stress is the ideal strength of a material which is an inherent property of a given atomic and electronic structure as well as a natural upper bound on its strength [1, 2]. While the variation of electron density can alter ideal strength of some materials [3], those manipulations usually involve stoichiometric change which may alter the nature of chemical bonding between atoms in crystal. In this regard, graphene, a two-dimensional crystal with atomic thickness, is an ideal material to investigate electronic control of ideal strength because it allows very high level of charge doping without any sacrifice of atomic integrity through either field-effect transistor setups [4, 5] or alkali metal depositions [6]. Although there have been many studies about effects of mechanical perturbation on electron physics in graphene [7–12], the effect of electron density variation on the mechanical properties of graphene has not been known yet.

Graphene is also known to be the strongest material [13] and can maintain its pristine strength regardless of presence of large grain boundaries [14]. A recent nanoindentation experiment [13] reports that the intrinsic strength of graphene is 42 N m^{-1} at the nominal equibiaxial breaking strain of $\epsilon_{\text{max}} = 0.225$. This was followed by a theoretical calculation [15] showing $\epsilon_{\text{max}} = 0.15$ which is quite smaller than the measured value. It is unusual because usual materials under strain typically fail before they reach the ideal strength due to various reasons. Therefore considerations on the other external effects such as a doping are called for to understand the ideal strength of graphene further since graphene samples in experiments are typically doped chemically or electronically.

In this paper, we report a theoretical study showing that graphene under equibiaxial strain becomes to be stronger as doping increases regardless of the charge character of doping, electron or hole. Though the ideal strength under equibiaxial strain increases slightly by

$1 \sim 6 \%$ depending on doping type and amounts, the corresponding critical breaking strain increases dramatically by $\sim 20 \%$ within the doping level of $\sim 3 \times 10^{14}/\text{cm}^2$ which is accessible in experiments [5, 6]. We show that the failure of isotropically expanded graphene through the A'_1 phonon mode softening [15] or the two-dimensional Peierls instability [16] is overcome by doping because the Fermi level of doped graphene lies outside the energy gap associated with the A'_1 phonon. On the contrary, under uniaxial strain invoking elastic failure of graphene [15], we find that electron doping weakens graphene by $5 \sim 7\%$ while hole doping strengthens one by $3 \sim 6\%$. The corresponding breaking strains also change a lot by 37% as doping swept from 0.05 holes to 0.05 electrons per carbon atom. Because the elastic failure under uniaxial strain is associated with occupation of the σ^* band [10], the asymmetric dependence of ideal strength on electron and hole doping can be explained in term of doping induced occupation (electron doping) or depopulation (hole doping) of the σ^* band of uniaxially strained graphene.

Our first-principles calculations [17] are carried out with plane wave basis and norm-conserving pseudopotentials [18]. The local density approximation (LDA) is used for the exchange-correlation functional [19]. Phonon spectrum is also calculated using density functional perturbation theory [17, 20]. The energy cutoff for expansion of the plane wave basis set is 80 Ry . The k -point grid of $48 \times 48 \times 1$ is used for the electronic structure and ionic structure relaxation calculations. Adjacent graphene layers in neighboring supercells are $8 \text{ \AA}$ away to avoid spurious interactions between them. Hole and electron doping is simulated within the rigid band approximation which is successfully used in recent studies on Kohn anomaly of doped carbon nanotubes [21] and doped graphene [22] respectively. For phonon dispersion, $12 \times 12 \times 1$ q -point sampling is used. Near the Kohn anomaly where the change of phonon frequency is very abrupt in a narrow momentum window, the explicit phonon calculations are

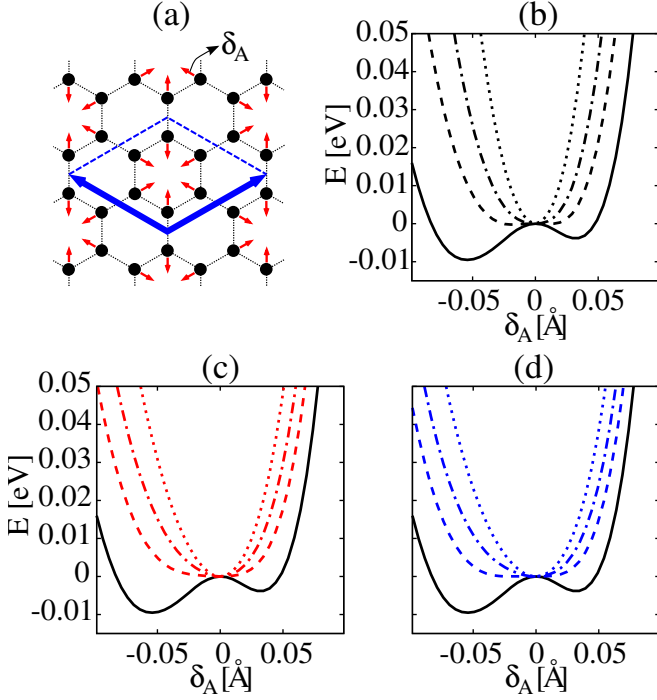


FIG. 1: (Color online) (a) Atomic displacements (red arrows) associated with the A'_1 phonon mode with an amplitude δ_A . The thick blue vectors indicate the K -point supercell of graphene. (b) The total energy change as a function of δ_A under various equibiaxial strains (ϵ). From top to bottom lines, $\epsilon = 0.12, 0.14, 0.15$, and 0.16 . (c) and (d) show the same curves as in (a) at a fixed strain, $\epsilon = 0.16$, with changing electron and hole doping from top to bottom, $n_e(n_h) = 0.04, 0.02, 0.01, 0.00$ respectively.

additionally done along the high symmetry paths to avoid the inherent errors in interpolated phonon dispersions.

When graphene expands isotropically, the A'_1 phonon mode (hexagonal breathing mode) at the K point softens and then becomes to be unstable at a certain critical equibiaxial strain [15]. The structures in Fig. 1 (a) show schematically how the crystal structure of graphene is deformed when the A'_1 phonon is excited. Here, the strain is defined by $\epsilon = (a - a_0)/a_0$, where a and a_0 are the lattice constant of equibiaxially strained graphene and that of pristine graphene respectively. In Fig. 1 (b), the total energy change as a function of the structural deformation of A'_1 phonon mode shows that, for $\epsilon > 0.15$, the hexagonally deformed structures are energetically more stable than the symmetric one [15]. For these calculations we use the K -point supercell in which six carbon atoms are included as shown in Fig. 1(a) [15]. This can be understood as two-dimensional extension of Peierls instability [16]. A half-filled pristine graphene has its Fermi level at the Dirac point and the excitation of A'_1 phonon mode generates a dynamical energy gap at the Dirac point [16, 23] realizing the Kohn anomaly at the K -point [23, 24]. As graphene expands over critical equi-

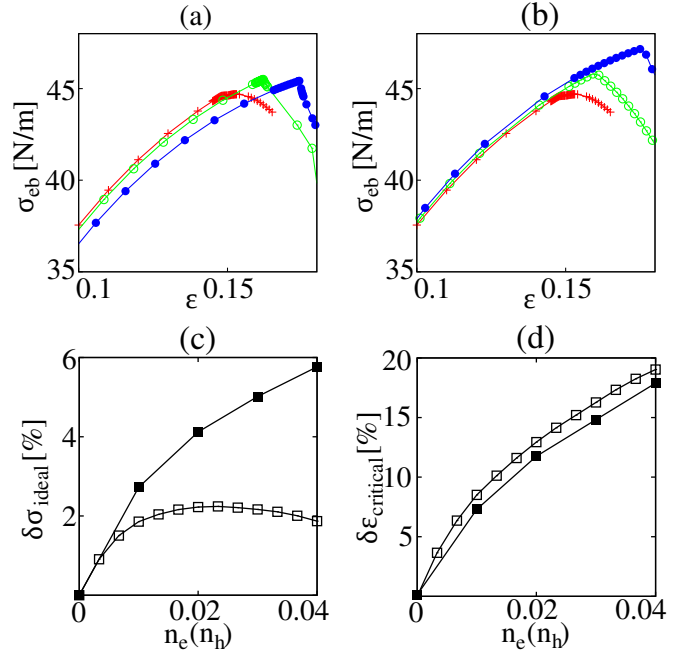


FIG. 2: (Color online) (a) and (b) show the stress-strain relationship with different electron and hole doping levels respectively. The red crosses are for undoped graphene for both (a) and (b). The equibiaxial strain is defined by $\sigma_{eb} \equiv \sqrt{\sigma_x^2 + \sigma_y^2}/\sqrt{2}$. In (a), $n_e = 0.013$ (open green circles) and 0.04 (solid blue). In (b), $n_h = 0.01$ (open green) and 0.04 (solid blue). The change of (c) ideal strength ($\delta\sigma_{ideal}$) and (d) corresponding critical breaking strain ($\delta\epsilon_{critical}$) of doped graphene with respect to those of undoped one in percentage as a function of $n_e(n_h)$. In both plots, the empty (filled) rectangles are for electron (hole) doped graphene.

axial strain, the energy gain through formation of static energy gap at the K -point overcomes the energy cost from ion-ion interaction so that the hexagonal network of graphene breakdowns [15, 16]. Therefore, if the Fermi level shifts away from the Dirac point by doping, the Peierls instability will be avoided by hardening the A'_1 phonon mode so that graphene becomes more resistive against the applied equibiaxial strain.

To confirm the doping related stability, we calculate the total energy of doped graphene with the A'_1 phonon mode. As discussed, Fig. 1 (b) shows the lattice instability of undoped graphene over a critical equibiaxial strain ($\epsilon > 0.15$). We have done the same calculations for doped graphene at various doping levels with a fixed overcritical strain of $\epsilon = 0.16$ [Figs. 1 (c) and (d)]. The electron (hole) doping level, $n_e(n_h)$, is defined by the number of additional electrons (holes) per a carbon atom. We note that $n_e = 0.01$ corresponds to 3.848×10^{13} electron/cm². As shown in Figs. 1 (c) and (d), the electron and hole dopings recover the stability of A'_1 phonon mode even at the strain of $\epsilon = 0.16$ under which pristine graphene is already broken.

To obtain complete ideal strengths and corresponding

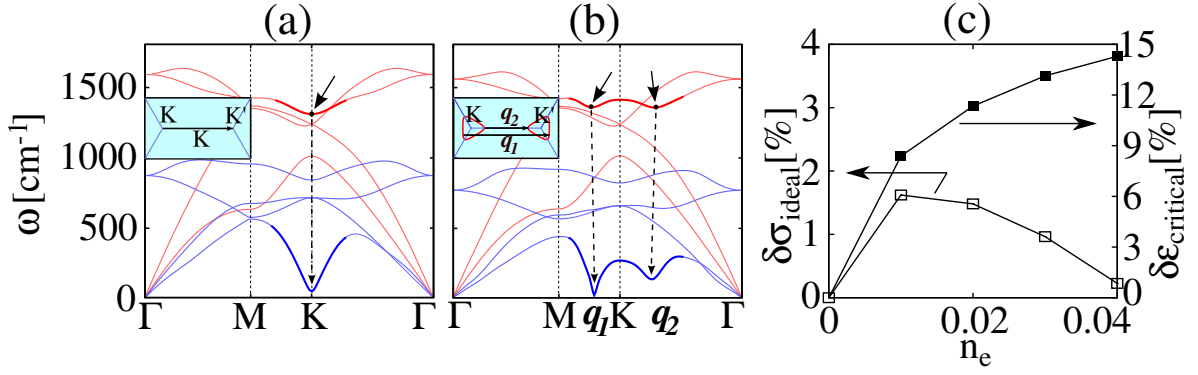


FIG. 3: (Color online) Phonon dispersion of (a) undoped and (b) electron-doped graphene ($n_e = 0.04$). In both cases, red (blue) curves are for graphene with (without) equibiaxial strain ((a) $\epsilon = 0.148$ and (b) $\epsilon = 0.167$). The black arrows indicate the Kohn anomaly. The inset for each plot shows the vectors (black arrows) connecting Fermi surfaces (red solid lines) inducing the Kohn anomaly. Here we do not show irrelevant out-of-plane phonon mode spectrum. (c) $\delta\sigma_{\text{ideal}}$ (empty rectangles) in the left ordinate and $\delta\epsilon_{\text{critical}}$ (filled rectangles) in the right one obtained from phonon dispersions as function of n_e (abscissa).

critical breaking strains as function of doping, the stress-strain calculations are needed because the total energy calculations only indicates structural instability. In the stress-strain relationship, the maximum stress at the critical breaking strain is the ideal strength of doped and undoped graphene. Figs. 2 (a) and (b) show representative stress-strain curves of strained graphene with the electron and hole doping respectively. It is noted that the stress maximum corresponding to the ideal strength shifts toward larger strain as the doping level increases independent of the doping type. We obtain the ideal strength and the corresponding critical breaking strain as a function of doping by taking the stress maximum values in Figs. 2 (a) and (b). The ideal strength (σ_{ideal}) of undoped graphene is found to be 44.6 N/m agreeing well with a recent experiment [13] and calculation [15]. The critical breaking strain, however, is $\epsilon = 0.148$ much smaller than the measured value [15, 16]. As n_e increases from 0.00 to 0.04, σ_{ideal} increases by $\sim 2\%$ ($n_e = 0.02$) and then decreases. As n_h increases from 0.00 to 0.04, σ_{ideal} increases monotonically by $\sim 6\%$ [Figure 2(c)]. Contrary to that, the critical breaking strain ($\epsilon_{\text{critical}}$) shows a dramatic increase by $\sim 18\%$ ($\epsilon_{\text{critical}} \sim 0.18$) as both n_e and n_h increase to 0.04 [Figure 2(d)].

We have further calculated phonon dispersions in order to see how the phonon softening at the K -point is affected by the doping. Softening of phonon to the negative phonon frequency may precede or indicate the instability of crystal structure [25]. Fig. 3 (a) shows the phonon dispersion of graphene with $\epsilon = 0$ (red) and $\epsilon = 0.148$ (blue) agreeing well with a previous study [15]. The frequency dip at the K -point associated with the A'_1 mode is the Kohn anomaly [23, 24]. We note that the LDA is not quantitatively perfect to describe the anomaly [26] but is sufficient to describe the softening within a certain error bar [15]. The Kohn anomaly occurs only for $\mathbf{q}$ when two electronic states at $\mathbf{k}_1$ and $\mathbf{k}_1 + \mathbf{q}$ are on the

Fermi surface [24, 27]. In undoped graphene, the Fermi surface is at the Dirac points located at $\mathbf{K}$ and $\mathbf{K}' = 2\mathbf{K}$ so that $\mathbf{q} = 0$ (Γ -point) and $\mathbf{q} = \mathbf{K}$ (K -point) are allowed for the anomaly. The inset in Fig. 3 (a) shows the corresponding vector $\mathbf{K}$ in the BZ. As graphene doped, the momentum at which the Kohn anomaly occurs shifts from the K -point and splits into two points. The A'_1 phonon hardens also because of change of the Fermi surfaces. In the red curve in Fig. 3 (b) for electron-doped graphene ($n_e = 0.04$), the Kohn anomaly occurs both at q_1 between M and K and at q_2 between K and Γ . The inset in Fig. 3 (b) shows the corresponding vectors $\mathbf{q}_1$ and $\mathbf{q}_2$ connecting the two electronic states at Fermi surfaces of two valleys in doped graphene. As the equibiaxial strain increases, the phonon at q_1 softens to zero frequency at the strain of $\epsilon = 0.167$ [blue line in Fig. 3 (b)]. This indicates that the doped graphene becomes structurally unstable through the less symmetric phonon mode at q_1 than A'_1 mode. The strain value of 0.167 for $n_e = 0.04$ doping differs from the corresponding critical breaking strain (0.179) obtained from the direct total energy calculation and stress-strain relationship [Fig. 2 (d)].

By taking stress and strain values when the softened phonon mode touches zero frequency, we can obtain the ideal strengths and the corresponding critical breaking strains as function of electron doping. As shown in Fig. 3 (c), the overall behaviors of $\delta\sigma_{\text{ideal}}$ and $\delta\epsilon_{\text{critical}}$ are similar to those obtained (Figure 2 (c) and (d)) from the stress-strain curves. However, the ideal strength increases only by $\sim 1.7\%$ and then decreases back to the original value as n_e reaches 0.04 [Figure 3(c)]. The corresponding breaking strain shows the monotonic increase by $\sim 15\%$. So, we can conclude that under equibiaxial strain the electron and hole doping improve the ideal strength slightly or at least maintains its undoped value while the corresponding critical breaking strain increases dramatically by doping. These interesting behaviors of

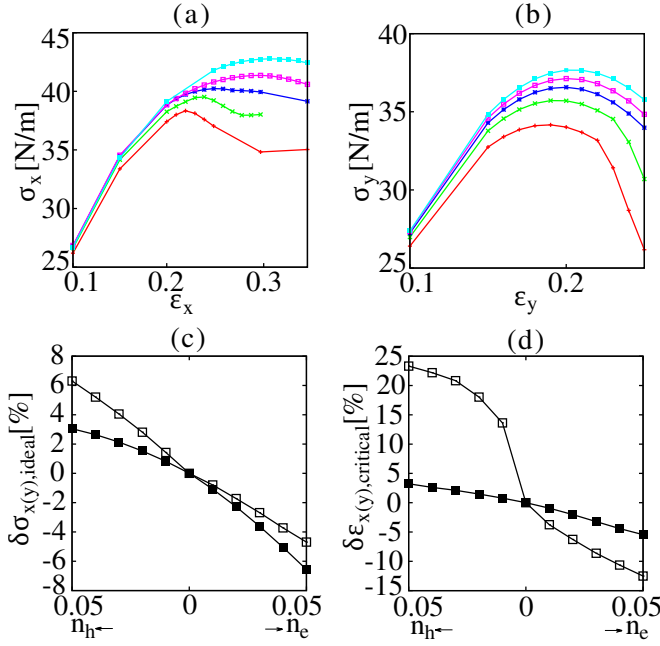


FIG. 4: (Color online) Stress-strain curves for graphene under (a) zigzag and (b) armchair strain with various doping levels. The doping levels are $n_h = 0.05, 0.02$, undoped, $n_e = 0.02, 0.05$ from the top to the bottom for both plots. (c) The change of ideal strength and (d) critical breaking strain as a function of the doping level for the zigzag (open rectangles) and armchair (solid ones) strain respectively.

stress and strain of doped graphene can be understood by noting that the ideal strength is mostly determined by σ bonds between carbon atoms that does not be affected much by the doping but that the breaking point of strain is determined by π bands owing to the Kohn anomaly that changes greatly according to the doping.

Next, we have analyzed the ideal strength of doped graphene under uniaxial strain. Unlike equibiaxial strain case, the uniaxial strain breaks the crystal symmetry of graphene. Thus, under uniaxial strain, the pristine isotropic Dirac cone moves away from K -point and distorts into anisotropic form with direction dependent electron group velocity [9, 10]. Here we only consider uniaxial strains either along zigzag direction or armchair direction [9, 10]. The former and the latter are called as zigzag and armchair strain respectively. We calculate the stress-strain relationship to find out the doping dependent ideal strength under uniaxial strains. For these calculations, the primitive unit cell including two carbon atoms is used since uniaxially strained graphene breaks down elastically unlike equibiaxial strain cases [15]. Fig. 4 (a) and (b) show the stress-strain curves for the zigzag and armchair strain respectively with different doping levels. It is found that the ideal strength under zigzag strain is substantially more sensitive to the doping than that under the armchair one. Figs. 4 (c) and (d) show the change of ideal strength and critical strain as function of dopings

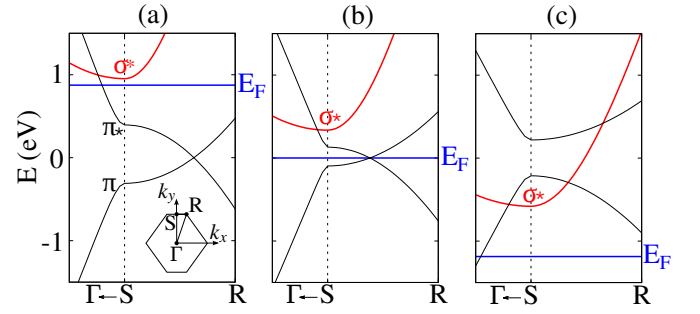


FIG. 5: (Color online) Electronic band structures of graphene under (a) the zigzag strain of $\epsilon = 0.25$ without doping, (b) $\epsilon = 0.22$ with electron doping $n_e = 0.05$ and (c) $\epsilon = 0.30$ with hole doping $n_h = 0.05$. The red and black lines are the σ^* and π (π^*) bands respectively and the blue is the Fermi level. The inset in (a) shows the high symmetry points of BZ of uniaxially strained graphene.

respectively. Contrary to the equibiaxial strain case, the response of graphene under uniaxial strain is asymmetric with respect to the electron and hole doping; graphene becomes stronger with the hole doping while it becomes weaker under the electron doping for both directions. For undoped graphene, the maximum stress of $\sigma_{ideal} = 40.2$ (36.6) occurs at $\epsilon_{critical} = 0.253$ (0.198) for the zigzag (armchair strain) agreeing with a previous study [28]. As in the case for doped graphene under the equibiaxial strain, the doping changes the strain values a lot while the ideal strength changes a little upon doping [Figs. 4(c) and (d)]. Under zigzag strain, the critical breaking strain increases from 0.253 to 0.311 (23% increase) as the hole doping reaches $n_h = 0.05$, and decreases to 0.22 (13% decrease) as the electron doping reaches $n_e = 0.05$. On the other hand, under the armchair strain, it increases only by 3.5% and decreases by 5% in the same condition.

Especially under the zigzag strain, the two Dirac cones at the K - and K' -point approach each other and eventually merge after a critical strain [9, 10, 29]. This opens a small energy gap at the merged point [9, 10]. At the same time, however, the energy of σ^* band is lowered toward the Fermi level [10] signaling the breakdown of crystal structure of graphene. Our calculation shows that the stress maximum occurs as the unoccupied σ^* band reaches the Fermi level. Figs. 5 (a), (b) and (c) show the electronic band structure for electron-doped, undoped, and hole-doped graphene under the zigzag strain respectively. For the electron doping with $n_e = 0.05$ the σ^* band is closer to the Fermi level compared with one in undoped graphene under zigzag strain so that the band is filled up at a relatively lower strain of $\epsilon = 0.22$ [Fig. 5 (b)]. Contrary to that, for the hole doping with $n_h = 0.05$ the σ^* band moves away from the Fermi level so that it requires relatively higher strain of $\epsilon = 0.30$ for the band to be filled up [Fig. 5 (c)]. This explains the physical origin of electron-hole doping asymmetry of the ideal strength

of doped graphene under zigzag strain.

Lastly, we discuss a possible solution to the aforementioned discrepancy between the recent experiment [13] and theories [15, 16] on the ideal strength of graphene. From our calculations, we note that the typical electron doped graphene can exhibit a theoretical ideal strength ($> 40 \text{ N m}^{-1}$) with an enhanced critical breaking equibiaxial strain, which is compatible with the experiment observation [13]. Though there is still quantitative difference in values of critical breaking strain between our theoretical estimation and experimental observation [13], the doping should play a major role to enhance the breaking strain and other unknown experiment factors such as anisotropy in applied forces [13] or formation of dislocation [14] may enhance the value further.

In conclusion, we have studied the effect of doping on the mechanical properties of graphene. Electron- and hole-doped graphene is shown to improve or maintain its ideal strength under equibiaxial strain while the corresponding breaking strain increases dramatically. So, it sets a new bound on the ideal strength and critical strain of isotropically expanded graphene in realistic situations. Furthermore, we demonstrate that the uniaxially strained graphene can decrease or increase the ideal strength and critical strain depending on the doping type. We believe that the present study not only highlights unique manifestation of electron and phonon physics of graphene but also can extend to explore interesting interplay between electronic degree of freedom and mechanical properties of other two dimensional crystals [30].

This work is supported by the NRF of Korea grant funded by MEST (QMMRC, No. R11-2008-053-01002-0 and CASE, No. 2011-0031640). Computational resources have been provided by KISTI Supercomputing Center (Project No. KSC-2011-C1-21) and the CAC of KIAS.

* Electronic address: hand@kias.re.kr

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